

ABSTRACT OF THE DISCLOSURE

In a semiconductor integrated circuit, a P-type epitaxial layer is provided on the entire surface of a P-type bulk substrate. The resistivity of the P-type bulk substrate is set to $1000\Omega\cdot\text{cm}$, and the thickness and the resistivity of the P-type epitaxial layer is set to $5\mu\text{m}$ and $10\Omega\cdot\text{cm}$, respectively. Then, a digital section and an analog section are provided remote from each other on the P-type epitaxial layer, where a digital circuit and an analog circuit are formed on the digital section and analog section, respectively. Further a device isolation region reaching the P-type bulk substrate is formed in a region between the digital section and analog section of the P-type epitaxial layer.